

United States Divisional Patent Application for:

**METHOD FOR CHEMICAL-MECHANICAL JET ETCHING
OF SEMICONDUCTOR STRUCTURES**

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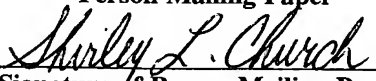
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1 **METHOD AND APPARATUS FOR CHEMICAL-MECHANICAL JET**
2 **ETCHING OF SEMICONDUCTOR STRUCTURES**

3 **BACKGROUND OF THE INVENTION**

4 [0001] Field of the Invention

5 [0002] This invention relates to a method and an apparatus for achieving chemical-
6 mechanical jet etching of features in a workpiece such as a semiconductor substrate or a
7 built-up stack of films. In particular, the invention permits high etch rates for thinning the
8 workpiece or for production of relatively large dimension etched features in such a
9 workpiece, such as trenches and through-wafer vias for electrical contacts, or reservoirs for
10 ink-jet heads, where critical dimensions are relatively large, on the order of 1-100 microns,
11 or for thinning in the range of 100-1000 microns.

12 [0003] Brief Description of the Background Art

13 [0004] Various wet-chemical etching, dry-etching (i.e., various forms of plasma etching)
14 and electrochemical methods exist which permit creation of features on a semiconductor
15 substrate or on a stack of layers of semiconductor, conductor, and dielectric materials, or
16 similar flat structure, generally using various sorts of patterned masks to control where
17 underlying material is etched away and where it is left in place. Such methods provide the
18 required degree of precision for etching semiconductor features with critical dimensions in
19 the submicron range, but typically achieve etch rates in the range of about 1 micron or less
20 of thickness per minute. Where the required features are relatively large-scale, in the range
21 of from about 10 to about 100 microns, as in making a through-wafer via or large trench on
22 a silicon wafer, or the amount of material to be removed is large, as in wafer thinning
23 applications, and the required precision is less critical, the etch rates achievable by such
24 methods are generally too low to be practical in commercial production. What is needed
25 is a method permitting the removal of large amounts of silicon wafer or other material, with

1 moderate precision, at etch rates sufficiently rapid to be practical in industrial semiconductor
2 processing.

3 SUMMARY OF THE INVENTION

4 [0005] We have invented a chemical-mechanical jet etching method which is capable of
5 quickly and accurately removing large amounts of material from a workpiece in wafer
6 thinning applications, and is capable of rapidly producing large-scale features, with critical
7 dimensions on the order of 1-100 microns, and aspect ratios (defined as the ratio of the depth
8 of an etched feature to the maximum diameter of a via, or the maximum width of a trench,
9 at the entrance) in the range of 1:1 to 10:1. The method of the invention can be carried out
10 on a generally flat semiconductor workpiece, including but not limited to a silicon wafer or
11 gallium arsenide or other semiconductor substrate, silicon-on-insulator ("SOI"), SiO₂, glass,
12 quartz, pyrex, ceramic, or glass bonded to a substrate, conductor, or insulator. In particular,
13 the method is expected to function very advantageously when applied to silicon wafer,
14 gallium arsenide, and SOI substrates. In both thinning and feature creation applications,
15 etch rates of at least about 10-100 microns of substrate thickness per minute can be achieved.

16 [0006] The method uses an ejector, typically a nozzle or array of nozzles, to deliver a jet,
17 a high-pressure stream of a fluid etchant medium, referred to in this application as the
18 "machining etchant," to the surface of a workpiece. Material is thereby machined from the
19 surface, at a rate as high as about 100 microns of depth per minute, in areas of the substrate
20 upon which the jet impinges. The areas which are not to be etched may be shielded from
21 the jet by a patterned mask, or the jet may simply be directed at those specific areas from
22 which material is to be removed, depending on the size of the desired feature or etching area.
23 As described above, the desired features may be on a workpiece such as a silicon wafer,
24 SiO₂, gallium arsenide substrate, or silicon-on-insulator substrate. For example, and not by
25 way of limitation, machined features created on a semiconductor substrate wafer may

1 include a through-wafer via for making an electrical connection from one surface of the
2 wafer to the other, or a large trench of the kind used in formation of conductor lines which
3 run across a surface of the wafer, or other three-dimensional shape to be created on the
4 workpiece. The method may also be used to remove material from the surface of a
5 workpiece which is to be thinned to a smaller thickness.

6 [0007] The apparatus used to carry out the method may provide for the use of a single
7 ejector, generally a nozzle or an array of nozzles. Each nozzle may be a single nozzle, or
8 a dual nozzle, designed to deliver a compound jet of machining etchant to the workpiece
9 The nozzle or nozzles may be stationary or movable. The workpiece may likewise be
10 stationary or movable. The workpiece may be rastered, rotated, or translated at an angle
11 with respect to a stationary nozzle or nozzles, or the nozzles moved with respect to a
12 stationary workpiece, or both may be moved.

13 [0008] The machining etchant used to carry out the invention may be a chemically inert
14 liquid, which merely acts to bombard the surface, or a liquid solution of a typical chemical
15 etchant, which bombards but also chemically reacts with the surface. The machining etchant
16 may be a slurry, including a suspension or dispersion, of abrasive or other solid particles in
17 a liquid or a gas medium. The slurry may include a chemical etchant, or may rely solely on
18 the presence of solid particles to provide physical bombardment. The chemical etchant, if
19 used, may be a liquid, or it may be a solution of an etchant compound dissolved in the liquid
20 component of the slurry, or it may be some or all of the solid particle component of the
21 slurry. In the case of the suspension or slurry, the particulates present in the machining
22 etchant can be of any appropriate chemical composition, particle size, particle size
23 distribution, or shape. The machining etchant may also be a dry powder, used for physical
24 bombardment and/or chemical reactivity, and carried by a high-pressure gas stream.

25 [0009] Jet etching can be done by direct-writing to the surface to be etched, or using a mask,
26 patterned so as to permit impingement of the etchant only in those areas of the workpiece
27 where material is to be removed. The mask, if any, covering that portion of the workpiece

1 surface where no etching is desired may be a photoresist mask, an inorganic hard mask, or
2 other protective mask. Following jet etching, the mask may be removed, if desired, using
3 an appropriate solvent and/or dry etch process, as applicable, to remove residual mask
4 material.

5 [0010] In one exemplary embodiment of the invention, the workpiece is a silicon or other
6 semiconductor substrate wafer. The machining etchant is a slurry of abrasive or physical
7 bombardment particulate material, carried in a liquid, which may also be a chemical etchant
8 or solution of a chemical etchant. The particulates may be selected from among the
9 following materials: fumed silica, cerium oxide, alumina, diamond, green or black silicon
10 carbide, boron cagernet, or other similar fine-grained hard materials. Specific materials are
11 expected to be particularly suitable for use with specific workpiece compositions, as is
12 known to persons skilled in the semiconductor art. The liquid may be selected from among
13 the following materials: Water can be used where minimal or no chemical component, but
14 only mechanical etching, is desired. The chemical etchants that may be used as the slurry
15 liquid are selected from among solutions of the following materials: KOH, NaOH, HF, HNA
16 (an aqueous solution of about 7 wt % HF, about 30 wt.% HNO₃, and about 10 wt.%
17 CH₃COOH), TMAH (tetramethyl ammonium hydroxide), EDP (ethylene diamine
18 pyrochatechol), and amine gallates. Again, specific etchants are expected to be particularly
19 suitable for carrying out the invention on specific workpiece compositions, as known to
20 persons skilled in the semiconductor art. In this embodiment, the nozzles are stationary, and
21 are arrayed across a diameter or a radius of the (usually circular) workpiece wafer. A mask
22 is applied over the surface of the workpiece wafer, and the wafer is rotated beneath (or
23 above) the nozzle array such that the machining etchant impinges upon non-masked areas
24 on the wafer surface facing the nozzles during each rotation of the wafer. Various methods
25 may be used to detect when the silicon wafer material in the non-masked areas has been
26 removed to the desired depth of a trench or other feature on the wafer surface, or when a
27 desired hole has been etched all the way through the wafer in order, for example, to create

1 a via extending from one surface of the wafer through to the other.

3 BRIEF DESCRIPTION OF THE DRAWINGS

4 [0011] Figure 1 presents a schematic drawing of an example apparatus for performing
5 the present invention's Chemical-Mechanical Jet Etching method upon a silicon wafer or
6 other relatively flat semiconductor structure. Figure 2 represents a schematic drawing of
7 a dual nozzle, a nozzle-within-a-nozzle, which can be used for delivery of machining
8 etchant, as described herein.

9 DETAILED DESCRIPTION OF THE INVENTION

10 I. DEFINITIONS

11 [0012] As a preface to the detailed description, it should be noted that, as used in this
12 specification and the appended claims, the singular forms "a", "an", and "the" include
13 plural referents, unless the context clearly dictates otherwise.

14 [0013] Specific terminology of particular importance to the description of the present
15 invention is discussed throughout the application.

16 II. APPARATUS FOR PRACTICING THE INVENTION

17 [0014] Figure 1 illustrates the general design of an apparatus capable of carrying out the
18 method of the invention. In operation, a silicon wafer or other workpiece (not shown) is
19 affixed to workpiece holder 101, which is capable of rotating, rastering, and/or
20 translating the workpiece. An etchant delivery system 109 carries a machining etchant
21 (not shown), pressurized by a machining etchant pump 111, from a machining etchant
22 reservoir 119, through an injector bar 105, to an array 107 of high pressure nozzles 103.
23 High pressure jets 108 of the machining etchant issue from the nozzles and impinge on

1 the surface of the workpiece, which is moving past the nozzles, etching away workpiece
2 material where the jets strike the surface. The jet etching process is carried on in a
3 closed, temperature- and pressure-controlled process chamber 117, which confines the
4 effluent machining etchant. Operating nozzle pressures of the machining etchant will
5 range from about 100 to about 10,000 psia, depending upon the composition of the
6 machining etchant and the size of the jet orifice (the higher the machining etchant
7 viscosity and the smaller the jet orifice, the higher the required nozzle pressure).
8 Typically, the nozzle pressure will range from about 100 to about 1000 psia for most
9 direct writing (maskless etching) operations, and from about 100 to about 500 psia for
10 jet etching using a mask.

11 [0015] If desired, the effluent etchant, which now carries the material etched off the
12 workpiece, can be returned, via a machining etchant collection and recycling system 115,
13 to the machining etchant reservoir 119, for recycling through the system. Meanwhile, an
14 endpoint detection system 113 can determine when the desired amount of material has
15 been removed from the workpiece, and either terminate the jet etching process
16 automatically, or provide information permitting an operator to do so manually.

17 [0016] In other variants of the apparatus, only a single machining etchant nozzle 103
18 may be used. In yet other variants, the nozzle 103 or nozzle array 107 may move in
19 addition to, or rather than, the workpiece holder 101, to produce the desired rotation,
20 translation, rastering, or other relative movement between the nozzles 103 and the
21 workpiece.

22 [0017] In another variation, the high pressure machining etchant nozzle 103 may be
23 designed as a dual nozzle, or nozzle-within-a-nozzle (see Figure 2), in which a
24 concentric annular outer orifice 201 surrounds a central orifice 203, and discharges a
25 secondary high-pressure flow of fluid 205, forming a spray curtain surrounding and
26 containing the jet cone 207 from the central orifice, thereby creating a more narrowly
27 focused jet. In addition, if each orifice of the dual nozzle has an independently operable

1 machining etchant delivery system 109 (in Figure 1), the dual nozzle may also be used to
2 simultaneously deliver a machining etchant of one composition and pressure from the
3 central orifice and a second machining etchant of a different composition and/or pressure
4 from the annular orifice, permitting adjustment of a resultant jet pattern, as well as
5 simultaneous or phased delivery jets of machining etchants with differing physical and/or
6 chemical properties from the two orifices, including, without limitation, jets of different
7 viscosities, densities, volatilities, temperatures, inert liquid or carrier gas compositions,
8 compositions of liquid chemical etchants and dissolved etchants, and compositions and
9 concentrations of particulate materials, including particle shapes, hardnesses, particle
10 size ranges and size distributions, colors, conductivities, and chemical reactivities. In
11 particular, in one advantageous embodiment of the dual nozzle, the pressures and
12 viscosities of the inner jet and the outer, annular jet, may be selected such as to produce a
13 distinct inner core and a higher viscosity annular cladding jet, which confines the core
14 jet, so as to achieve a very narrow, powerful jet for, e.g., fluid jet drilling or trenching
15 operations. When a dual nozzle is used to simultaneously deliver two different
16 machining etchants, it will generally not be appropriate to recycle the effluent machining
17 etchant. The dual nozzle (or a standard nozzle) may also be constructed so as to permit
18 an electrical bias potential to be applied between the jet nozzle and the workpiece,
19 further enhancing the etching by electrochemical reaction, with the inclusion of a
20 suitable electrolyte in the machining etchant stream.

21 [0018] In addition, a regulating mechanism, not shown but associated with the
22 machining etchant delivery system 109, may be provided to deliver the machining
23 etchant to all or selected nozzles, or to either or both of the orifices of a dual nozzle, in
24 such a manner as to cause the pressure and/or flow rate delivered by the nozzle or orifice
25 to vary while in operation, either continuously or in pulsed fashion. This will permit, for
26 example, on-the-fly transitions between different machining etchant compositions, or
27 delivery to the substrate surface of pulses of machining etchant in order to better remove

1 and clear away the effluent machining etchant, carrying etched workpiece material, from
2 the contact points at which jet etching is taking place.

3 EXAMPLES

4 [0019] Several examples of various embodiments of the invention are presented below,
5 illustrating particular features of the invention which are helpful for particular
6 applications of the invention.

7 [0020] Example 1 - Thinning

8 [0021] In a first embodiment of the invention, a silicon wafer, other semiconductor
9 substrate, or other workpiece, is uniformly thinned by using the apparatus shown in
10 Figure 1.

11 [0022] A workpiece (not shown) is affixed to the workpiece holder 101, and the holder
12 101 rotates the workpiece beneath the injector bar 105, with its array 107 of high-
13 pressure nozzles 103. A machining etchant, in the form of a slurry or suspension of
14 appropriate particulate material in a chemical etchant/solvent, in a concentration in the
15 range of from about zero to about 95 weight percent, is pumped by pump 111 through
16 delivery system 109 to nozzle array 107 on injector bar 105, at a nozzle pressure in the
17 range of about 7 to about 70 Kg/cm². Nozzles 103 then deliver the machining etchant
18 108 as a high-pressure jet which impinges upon the workpiece wafer as the holder 101
19 and workpiece rotate past the nozzles 103 at a speed ranging from about 100 to about
20 2000 RPM.

21 [0023] The angle at which the machining etchant 108 impinges on the workpiece
22 surface (not shown) should be in the range of between about 5° and about 15° from
23 perpendicular to the etched surface, in that it must be close enough to perpendicular to
24 avoid dissipating the force of the spray, whereas an angled surface impingement may
25 facilitate the clearing away of the sprayed machine etchant 108 and entrained etched
26 material from the workpiece surface. So long as an appropriate relative position between
27 the workpiece surface and nozzle array 107 is maintained, operation of the entire

1 assembly in an inverted position, with the workpiece rotating above rather than beneath
2 the nozzle array 107, or indeed at any convenient orientation of the workpiece, is
3 acceptable.

4 [0024] In this embodiment, no mask is applied to the surface of the workpiece. Instead,
5 the number, angle spread, and overlapping of the nozzles' 103 spray patterns are adjusted
6 to deliver, as nearly as possible, equal spray fluxes at all points on the workpiece, so that
7 the surface of the workpiece is uniformly machined (thinned) to the desired thickness.
8 Etch rates as high as about 100 microns of depth per minute are achievable.

9 [0025] The effluent machining etchant slurry, with removed workpiece material carried
10 in it, is transported within the process chamber 117, and collected in an effluent slurry
11 collector 115, from which it is optionally transported to a slurry tank 119, and recycled
12 through the system until it is determined to be chemically exhausted, physically
13 degraded, or loaded with removed material such that it should be discarded. The effluent
14 machining etchant may be recycled until it will no longer etch effectively, and then
15 replaced altogether, or it may be replenished by the periodic or automated addition, to the
16 slurry tank, of fresh chemical etchant, and/or new particulate material, either during
17 continuing etching operations, or after an appropriate number of etching runs. Note,
18 recycling of machining etchant would typically not be done where jet etching is carried
19 out using different machining etchants from the inner and outer orifices of the dual
20 nozzle design described earlier.

21 [0026] Typical ranges of process conditions for this embodiment of the method of the
22 invention are presented in Table I, below.

23 [0027] Table 1

24 Typical Process Condition Ranges for Chemical-Mechanical Jet Etching of a
25 Semiconductor Workpiece

Process Variable	Range of Process Variable in Jet Etching Operation
Machining Etchant Flow Rate (sccm)	About 0.1 to about 10
Machining Etchant Pressure (Psia)	About 100 to about 10,000; about 100 to about 1000 for direct writing applications; about 100 to about 500 for masked jet etching.
Identity of Liquid in Machining Etchant	Dependent on workpiece being etched
Identity of Chemical Etchant in Machining Etchant	Dependent on workpiece being etched, but typically KOH for a silicon substrate
Chemical Etchant Concentration in Machining Etchant (Wt. Percent)	Dependent on workpiece being etched, but typically about 33% KOH in water for a silicon substrate
Identity of Particulate Material in Machining Etchant	Dependent on workpiece being etched, but typically SiO ₂ for silicon substrate
Particulate Concentration in Machining Etchant (Wt. percent)	About 10 to about 75
Machining Etchant Temperature (°C)	about zero to about 80
Workpiece Temperature (°C)	About zero to about 100
Process Chamber Temperature (°C)	About 20 to about 80
Process Chamber Pressure (Atm. Absolute)	About 0.1 to about 1.1

[0028] Example 2 - Patterning

[0029] A second embodiment of the invention uses the same the general apparatus as is

1 illustrated by Figure 1, and operation as described in Example 1, but utilizes a patterned
2 mask applied to the surface of the semiconductor workpiece to permit selective etching
3 of a surface of that workpiece. Relatively large-scale features, such as trenches and vias
4 with critical dimensions in the range of from about 5 to several hundred microns, and
5 depths of up to the full thickness of the workpiece wafer, can be readily produced in this
6 way, again at etch rates as high as about 100 microns of depth per minute. Typical
7 process conditions for this embodiment of the method of the invention are also as
8 presented in Table I, above.

9 [0030] The patterned mask may consist of either a conventional organic photoresist, or a
10 glasslike silane material, or an inorganic hard mask, such as silicon oxide or silicon
11 nitride, which are generally known in the art.

12 [0031] This chemical-mechanical jet etch method is inherently anisotropic. If, as is
13 usually the case, a vertical feature sidewall is desired on the features being etched, the
14 angle between the discharge direction of the high-pressure nozzles¹⁰³ and the workpiece
15 surface must be more perpendicular than in wafer thinning operations, to avoid getting
16 either tapered or undercut feature profiles.

17 [0032] If the method is used to etch vias, up to and including through-wafer ones, either
18 perpendicular holes or holes angled up to about 15° from perpendicular to the wafer
19 surface are possible with appropriate selection of angle of machining etchant
20 impingement. Pulsed delivery of machining etchant may be used to avoid buildup of
21 etched material in the bottom of the hole, or stagnation of the etchant in the hole,
22 preventing the entry of fresh machining etchant.

23 [0033] Following completion of etching of the desired features, the patterned mask can,
24 depending on the application, either be left in place, or be stripped off the wafer by use
25 of an appropriate solvent, for an organic mask material, or by a wet- or dry-etch step with
26 an appropriate etchant, selected to avoid or minimize attack on the etched features, for a
27 hard mask.

1 [0034] Example 3 - Maskless Jet Etching.

2 [0035] A third embodiment of the invention again uses the basic apparatus illustrated in
3 Figure 1, but, as in the wafer thinning operations described in Example 1, uses no mask.
4 Instead, in this embodiment, intended for making multiple vias in or through a silicon
5 wafer or other semiconductor workpiece, the workpiece is held stationary, and a narrow
6 stream of machining etchant is directed, from a single narrowly-focused nozzle, at each
7 desired via location, serially with one nozzle or concurrently with multiple nozzles, until
8 the desired etch depth is achieved. Pulsed delivery of machining etchant, as described
9 above, may be advantageous to avoid buildup of machining etchant loaded with etched
10 material, or stagnation of the etchant, in the hole. Process conditions are again generally
11 those shown in Table 1. Features in the size range of about 10 μ or larger can be direct-
12 written in this way.

13 [0036] The narrowly-focused machining etchant stream of this embodiment may be
14 better achieved by utilizing a dual nozzle, or "nozzle within a nozzle" design, described
15 above and shown in Figure 2, wherein an outer annular orifice surrounds a central orifice
16 in each spray nozzle, producing a curtain of etchant from the annular orifice that acts to
17 restrain and focus the jet from the interior orifice in a tighter pattern, maintaining better
18 control over the diameter of the hole etched in the workpiece by the jet from that nozzle.
19 Such a nozzle will also permit "on the fly" transitions in the aggregate composition of
20 the machining etchant, changing, for example, to a greater or lesser solids concentration,
21 solids particle size distribution, or chemical etchant concentration, as discussed
22 previously, while etching continues, by permitting feeding different machining etchant
23 compositions to the central and to the annular nozzle orifices.

24 [0037] Example 4 - Trenching

25 [0038] Another embodiment of the invention, rather than using a mask and impinging
26 machining etchant on the entire surface of the workpiece to be etched, uses no mask, but
27 instead uses the narrowly-focused nozzle design discussed in Example 3 to permit

1 accurately-located removal of material by each nozzle, and moves either the nozzles 103 or
2 the workpiece holder 101, or both, during etching, such that their relative movement causes
3 trenches to be etched wherever the machining etchant impinges on the workpiece. In
4 particular, if either the workpiece holder 101 or the nozzles 103 is rastered with respect to
5 the other, parallel and/or perpendicular trenches of a desired depth can be achieved by
6 controlling the speed and direction of the relative movement of the nozzles 103 and the
7 workpiece holder 101, and the volume and composition of the machining etchant delivered.
8 Again, pulsed delivery of machining etchant may be helpful in avoiding buildup of sprayed
9 machining etchant and etched workpiece material.

10 [0039] Example 5 - Liquid Jet Etching

11 [0040] In another embodiment of the invention, no solid particulates are incorporated in the
12 machining etchant, which may comprise a chemical etchant, which may itself be a liquid or
13 a solute. Where the concentration of a chemical etchant material in the fluid is zero, the
14 fluid, delivered to the workpiece surface at high pressure and velocity, serves merely as a
15 bombarding agent. Increasing concentrations of chemical etchant materials in the machining
16 etchant will increasingly contribute chemical etching of the surface as well. The use of a
17 mask to protect areas of the workpiece where etching is not desired will be important, since,
18 where the bulk of the etching is being done by chemical and not mechanical action, the
19 chemical reaction will otherwise continue wherever chemical etchant remains in contact
20 with the workpiece surface. However, as the etching is increasingly accomplished by
21 chemical attack on the workpiece rather than by physical impingement upon it, the etching
22 action will be much more isotropic, so the use of a mask may be much less effective in
23 preventing undercutting in the sidewalls of the etched features.

24 [0050] Example 6 - Dry Etching

25 [0050] In another embodiment of the invention, no liquid chemical etchant or solvent is
26 used. Instead, the particulate etching medium is carried on a high-velocity gas stream. The

basic apparatus remains as illustrated in Figure 1, but the machining etchant is a dry powder, which impinges on the workpiece at high velocity. Generally, such etching will involve no chemical reaction with the surface, though it is possible to select particulate species which chemically react with the workpiece surface when brought into intimate contact with it. Modes described above, either with or without the protective mask, are equally applicable with dry powder etch. Typical process conditions will differ from those used with the liquid slurries or suspensions, and are presented in Table 2, following.

[0052] Table 2

Typical Process Conditions for Chemical-Mechanical Jet Etching of a Semiconductor Structure. Utilizing a Dry Powder Machining Etchant

Process Variable	Range of Process Variable in Jet Etching Operation
Machining Etchant Flow Rate (sccm)	About 0.1 to about 10
Machining Etchant Pressure (Psia)	about 100 to about 10,000; more typically about 100 to about 1000
Identity of Machining Etchant Carrier Gas	Typically N ₂ or air
Identity of Machining Etchant Particulate Material	Dependent on workpiece composition, but typically SiO ₂ for a silicon substrate
Particulate Concentration in Machining Etchant (Vol. percent)	About 80 to about 90
Machining Etchant Temperature (°C)	About 0 to about 80
Workpiece Temperature (°C)	About 0 to about 100

1	Process Chamber	About 20 to about 80
2	Temperature	
3	(°C)	
4	Process Chamber	About 0.1 to about 1.1
5	Pressure	
6	(Atm. Absolute)	

7 [0053] The above described preferred embodiments are not intended to limit the scope
8 of the present invention, as one skilled in the art can, in view of the present disclosure,
9 expand such embodiments to correspond with the subject matter of the invention claimed
10 below.